AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning on page 25, line 19 through page 26, line 2 as shown below:

Fig. 1 is a cross-sectional view of the substantial part of a dye sensitized wet-type photoelectric conversion device according to an embodiment of the invention; Fig. 2 is a cross-sectional view of the substantial part of a dye sensitized wet-type photoelectric conversion device according to an embodiment of the invention; and ~~Figs.~~ Fig. 3A and Fig. ~~3A~~ 3B are cross-sectional views for explaining a manufacturing method of a dye sensitized wet-type photoelectric conversion device according to an embodiment of the invention.

Please amend the paragraph beginning on page 26, lines 10-26, as shown below:

As shown in Fig. 1, in the dye sensitized wet-type photoelectric conversion device, a transparent conductive substrate 1, having a semiconductor nanoparticle layer 2 (semiconductor electrode) retaining a sensitizing dye thereon, and a transparent conductive substrate 3, having ~~a platinum or platinum catalyst layer 5~~ a platinum or platinum catalyst layer 4 thereon, are put together such that the semiconductor nanoparticle layer 2 and the platinum or platinum catalyst layer 4 face to each other via a predetermined distance. In a space between them, an electrolyte layer (electrolytic solution) 5 is enclosed. The electrolyte layer 5 is sealed by a predetermined seal member, not shown. The semiconductor nanoparticle layer 2 is formed by pressing a paste already retaining a sensitizing dye and containing semiconductor nanoparticles dispersed therein with a press.

Please amend the paragraph beginning on page 27, line 17 through page 28, line 6 as shown below:

First prepared is the transparent conductive substrate 1. Next as shown in Fig. 3A, paste 6 containing a binder and containing dye-retained semiconductor nanoparticles dispersed therein is coated on the transparent conductive substrate 1 with a predetermined gap (thickness). The paste 6 is next pressed by a predetermined method with predetermined pressure while heated to a temperature in the range from 30°C to lower one of the softening temperature of the transparent conductive substrate 1 and the deactivation temperature of the sensitizing dye, or more preferably in the range from 50°C to 120°C. The pressure for the press is 500 kg/cm^2 or more, or

more preferably in the range from 5000 kg/cm^2 to 20000 kg/cm^2. As a result of the hot press, ~~he~~ the dye-retained semiconductor nanoparticle layer 2 is bonded onto the transparent conductive substrate 1 as shown in Fig. 3B.

Please amend the paragraph beginning on page 35, lines 15-26, as shown below:

TiO_2 paste prepared in the same manner as that of Example 1 was directly coated on a conductive PET substrate (having sheet resistance of 50 Ω/□) having SnO_2 coating on its surface to be sized 1 cm x 1 cm and make the gap of 200 μm by blade coating, and pressure of 10000 kg/cm^2 was applied ~~too~~ to the paste for 30 seconds at 120°C by a press machine. On the dye-retained TiO_2 paste nanoparticle layer thus obtained, the same dye-retained TiO_2 paste was coated by another gap of 200 μm by blade coating to make a pressure-bonded dye-retained TiO_2 nanoparticle layer under the same conditions.